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## **Preliminary**

# **SGB-2433(Z)**

#### DC to 4GHZ ACTIVE BIAS GAIN BLOCK

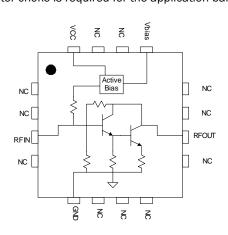
RFMD Green, RoHS Compliant, Pb-Free (Z Part Number)
Package: 3x3 QFN, 16-Pin

#### **Product Description**

RFMD's SGB-2433 is a high performance SiGe HBT MMIC amplifier utilizing a Darlington configuration with an active bias network. The active bias network provides stable current over temperature and process Beta variations. Designed to run directly from a 3Vto5V supply the SGB-2433 does not require a drop resistor as compared to typical Darlington amplifiers. This robust amplifier features a Class 1C ESD rating, low thermal resistance, and unconditional stability. The SGB-2433 product is designed for high linearity 3V gain block applications that require small size and minimal external components. It is on chip matched to  $50\Omega$  and an external bias inductor choke is required for the application band.

Optimum Technology
Matching® Applied

GaAs HBT
GaAs MESFET
InGaP HBT
SiGe BiCMOS
Si BiCMOS
✓ SiGe HBT
GaAs pHEMT
Si CMOS
Si BJT
GaN HEMT
RF MEMS



#### **Features**

- High Reliability SiGe HBT Technology
- Robust Class 1C ESD
- Simple and Small Size
- $P_{1dB}$  = 6.9 dBm at 1950 MHz
- $IP_3$  = 18.0 dBm at 1950 MHz
- Low Thermal Resistance=221C/W

### **Applications**

- 3V Battery Operated Applications
- LO Buffer Amp
- RF Pre-Driver and RF Receive Path

Parameter	Specification			Unit	Condition	
Farameter	Min.	Тур.	Max.	Unit	Condition	
Small Signal Gain		19.1		dB	850MHz	
	15.7	17.2	18.7	dB	1950MHz	
		16.2		dB	2400 MHz	
Output Power at 1dB Compression		7.7		dBm	850MHz	
	5.4	6.9		dBm	1950MHz	
		6.2		dBm	2400MHz	
Output Third Order Intercept Point		19.5		dB	850MHz	
	16.0	18.0		dB	1950MHz	
		18.0		dB	2400MHz	
Noise Figure		3.5	4.5	dB	1950MHz	
Frequency of Operation	DC		4000	MHz		
Current, I <sub>C</sub>	21.0	25.0	29.0	mA		
Input Return Loss	10.0	13.4		dB	1950MHz	
Output Return Loss	10.0	13.6		dB	1950MHz	
Thermal Resistance		221		°C/W	junction to backside	

Test Conditions:  $Z_0 = 50 \Omega$ ,  $V_{CC} = 3V$ ,  $I_C = 25 \text{ mA}$ ,  $T = 30 ^{\circ}\text{C}$ 

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#### **Absolute Maximum Ratings**

Parameter	Rating	Unit
Current (I <sub>C</sub> total)	60	mA
Max Device Voltage (V <sub>D</sub> )	5	V
Max RF Input Power	20	dBm
Power Dissipation	0.2	W
Max Junction Temperature (T <sub>J</sub> )	150	°C
Operating Temperature Range (T <sub>L</sub> )	-40 to + 85	°C
Max Storage Temperature	-40to+150	°C

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one. Bias Conditions should also satisfy the following expression:  $I_DV_D\!<\!(T_J\!-\!T_L)/\,R_{TH},\,j\text{-}I$ 



#### Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

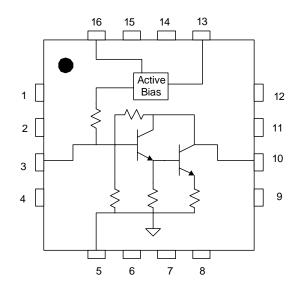
RoHS status based on EUDirective 2002/95/EC (at time of this document revision).

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#### Detailed Performance Table: V<sub>CC</sub>=3V, I<sub>C</sub>=25mA, T=25 °C, Z=50 $\Omega$

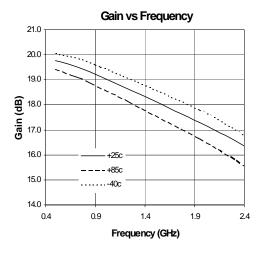
Parameter	Unit	100	500	850	1950	2400	3500
		MHz	MHz	MHz	MHz	MHz	MHz
Small Signal Gain (G)	dB	19.7	19.5	19.1	17.2	16.2	14.0
Output 3rd Order Intercept Point (OIP <sub>3</sub> )	dBm		20.0	19.5	18.0	18.0	
Output Power at 1dB Compression (P <sub>1dB</sub> )	dBm		8.3	7.7	6.9	6.2	
Input Return Loss (IRL)	dB	25.0	19.9	17.1	13.4	12.7	10.5
Output Return Loss (ORL)	dB	20.5	18.9	17.1	13.6	13.1	13.0
Reverse Isolation (S <sub>12</sub> )	dB	22.4	22.6	22.9	23.7	23.9	24.5
Noise Figure (NF)	dB	3.8	3.2	3.2	3.5	3.9	4.3

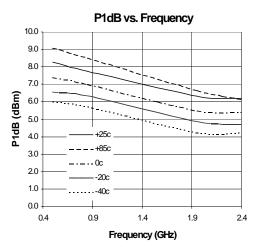
#### **Simplified Device Schematic**

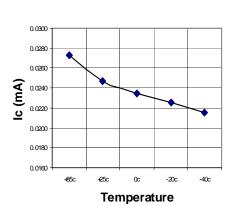




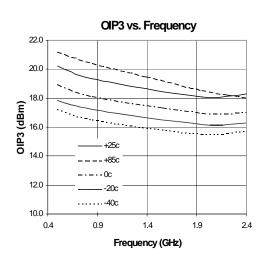
Evaluation Board Data ( $V_{CC} = V_{BIAS} = 3.0 \text{ V}$ ,  $I_C = 25 \text{ mA}$ ) Bias Tee substituted for DC feed inductor (L1)

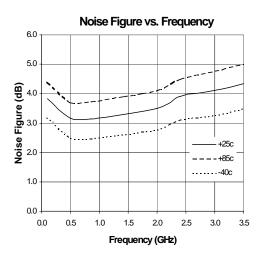


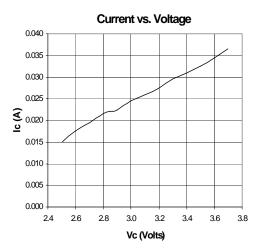




Ic vs. Temperature

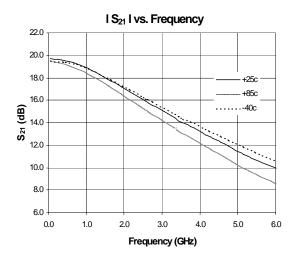


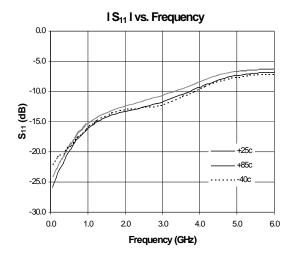


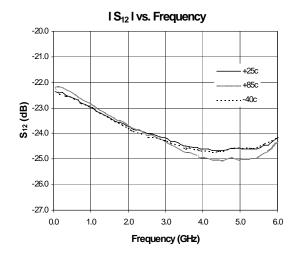


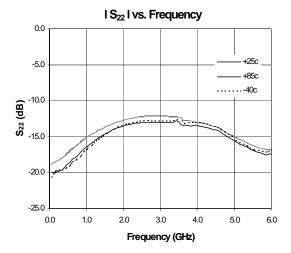


Evaluation Board Data ( $V_{CC} = V_{BIAS} = 3.0 \text{V}$ ,  $I_C = 25 \text{ mA}$ ) Bias Tee substituted for DC feed inductor (L1) cont.







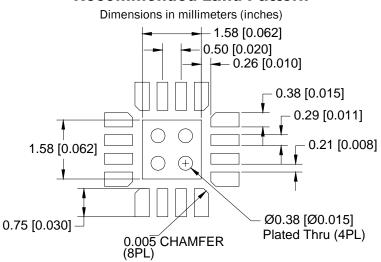




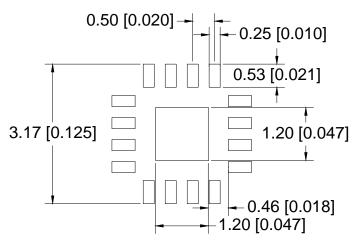
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Pin	Function	Description		
1, 2,	NC	These are no connect pins. Leave them unconnected on the PC board.		
4, 6,				
7, 8,				
11,				
12, 14				
3	RF IN	RF input pin. A DC voltage should not be connected externally to this pin		
5	GND	An extra ground pin that is connected to the backside exposed paddle. Connection is optional.		
10	RF OUT	RF Output pin. Bias is applied to the Darlington stage thru this pin.		
13	VBIAS	This pin sources the current from the active bias circuit. Connect to pin 10 thru an inductor choke.		
16	VCC	This is Vcc for the active bias circuit.		
Back-	GND	The backside exposed paddle is the main electrical GND and requires multiple vias in the PC board to GND. It is also the main thermal path.		
side		main diermai padi.		

#### **Recommended Land Pattern**



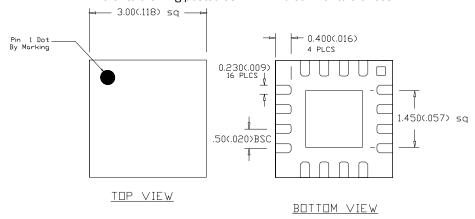
## **Recommended PCB Soldermask for Land Pattern**

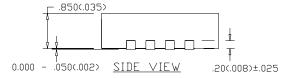




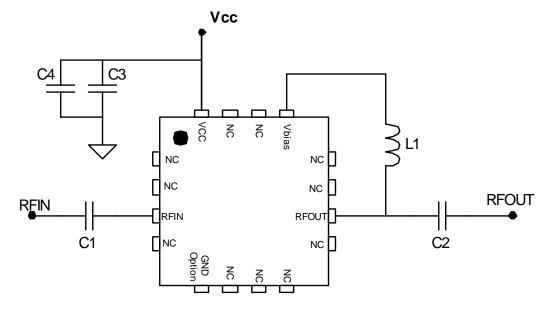
## **Package Drawing**

Dimensions in millimeters (inches) Refer to drawing posted at www.rfmd.com for tolerances.



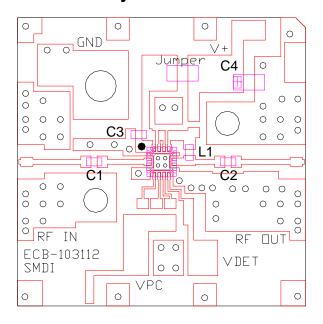


## **Typical Evaluation Board Schematic for 3.0V**





## **Evaluation Board Layout and Bill of Materials**



Board material GETEK, 31 mil thick, Dk = 4.2, 1 oz copper.

#### **Component Values By Band**

Designator	500 MHz	850 MHz	1950MHz	2400 MHz
C3	1000 pF	1000 pF	1000pF	1000 pF
C4*	1uF	1uF	1uF	1uF
C1, C2	220pF	68 pF	43pF	22pF
L1	68nH	33 nH	22nH	18nH

<sup>\*</sup>C4 is optional depending on application and filtering. Not required for SGB device operation.

Note: The amplifier can be run from a 5V supply by simply inserting a  $82\Omega$  resistor in series with  $V_{CC}$ .

#### **Part Identification**

The part will be symbolized with an "SGB2433" for Sn/Pb plating or "SGB24Z" for RoHS green compliant product. Marking designator will be on the top surface of the package.

## **Ordering Information**

Part Number	Reel Size	Devices/Reel
SGB-2433	13"	3000
SGB-2433Z	13"	3000

**SGB-2433(Z)** 

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